



			DB - I	Time stamp
L	Hits	Search Text	פע	Time Stamp
Number		susceptor and (sandblasting or blasted or	USPAT;	2003/03/10
1	16	blasting) and etch\$4 and (rinse or	EPO; JPO;	14:56
		rinsing)	IBM TDB	
_	25	susceptor same (sandblasting or blasted	USPĀT;	2003/03/10
2	25	or blasting)	EPO; JPO;	16:21
	ļ	•	IBM_TDB	
3	91	susceptor and (sandblasting or blasted or	USPAT;	2003/03/10
3	71	blasting)	EPO; JPO;	15:22
			IBM_TDB	2002/02/10
4	8	(susceptor or chuck or pedestal) same	USPAT;	2003/03/10
3		(glass or "silicon dioxide" or	EPO; JPO;	16:16
		"SiO.sub.2") same (sandblasting or	IBM_TDB	
	ļ	blasted or blasting)	TAC D D III	2003/03/10
5	329	(susceptor or chuck or pedestal) and	USPAT; EPO; JPO;	15:24
		lalage or "silicon dioxide" or	IBM TDB	13.23
		"SiO.sub.2") and (sandblasting or blasted	IBW_IDD	
		or blasting)	USPAT;	2003/03/10
6	160	((susceptor or chuck or pedestal) and	EPO; JPO;	15:25
		(glass or "silicon dioxide" or	IBM TDB	
		"SiO.sub.2") and (sandblasting or blasted	12122	
		or blasting)) and semiconductor (susceptor or "substrate holder" or	USPAT;	2003/03/10
7	18	pedestal) and (glass or "silicon dioxide"	EPO; JPO;	16:20
		or "SiO.sub.2") and (sandblasting or	IBM TDB	
		blasted or blasting) and etch\$4 and		
		(rinse or rinsing)		
	133	l' l'andelection or	USPAT;	2003/03/10
8	155	blasted or blasting)	EPO; JPO;	16:28
			IBM_TDB	0000 (00 (10
9	2030	(susceptor or jig) same etch\$4	USPAT;	2003/03/10
1		1	EPO; JPO;	16:29
			IBM_TDB	2003/03/10
10	12		USPAT;	16:31
		blast\$3	EPO; JPO; IBM TDB	10.51
		1.04	USPAT;	2003/03/10
11	32	(susceptor or jig) same etch\$4 same	EPO; JPO;	16:36
		(rinse or rinsing)	IBM TDB	
		" 'l' same blast\$4	USPAT;	2003/03/10
12	752	(SiC or "silicon carbide") same blast\$4	EPO; JPO;	16:37
			IBM TDB	
		((SiC or "silicon carbide") same blast\$4)	USPAT;	2003/03/10
13	51	and (susceptor or jig)	EPO; JPO;	16:37
		and (susceptor or)19/	IBM_TDB	
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